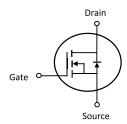
N Channel MOSFET

multicomp PRO



Device Schematic

RoHS Compliant



Applications

- · High Efficiency Switch Mode Power Supplies
- · Electronic Lamp Ballasts Based on Half Bridge
- · LED Power Supplies

Features

- $R_{DS(ON)} = 0.82\Omega$ @ $V_{GS} = 30V$
- · Ultra Low Gate Charge
- · Low Reverse Transfer Capacitance
- Fast Switching Capability
- · Avalanche Energy Specified
- · Improved dv/dt Capability, High Ruggedness

Maximum Ratings @TA = +25°C

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	Vos	650	V	
Gate-Source Voltage	Vgs	±30		
Avalanche Current (Note 2.)	lar	12		
Continuous Drain Current	lo	12	A	
Pulsed Drain Current (Note 2.)	Ідм	48	7	
Single Pulsed Avalanche Energy (Note 3.)	Eas	790	mJ	
Repetitive Avalanch9 Energy (Note 2.)	Ear	24		
Peak Diode Recovery dv/dt (Note 4.)	dv/dt	4.5	V/ns	
Power Dissipation	PD	51	W	
Junction Temperature	Tj	150	°C	
Operating Temperature Range	Topr	-55 to +150		
Storage Temperature Range	Тѕтс	-55 (0 + 150		

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L = 10mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25Ω , Starting T_J = 25° C
- 4. IsD ≤ 12A, di/dt ≤ 200A/µs, VDD ≤ BVDSS, Starting TJ = 25°C

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N Channel MOSFET



Electrical Characteristics @TA = +25°C

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
OFF Characteristics						
Drain-Source Breakdown Voltage	Vgs=0V, Ip=250µA	VDSS	650			V
Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =30V			_	100	nA
Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =-30V	lgss			-100	
Drain-Source Leakage Current	V _{DS} =650V, V _{GS} =0V	Ipss		İ	1	μA
Breakdown Voltage Temperature Coefficient	ID=250 μA,Referenced to 25°C	ΔBV _{DSS} /ΔT _J		0.7		
ON Characteristics						
Gate-Threshold Voltage	Vos=Vgs, Io=250µA	Vth(GS)	2		4	V
Static Drain-Source On-State Resistance	Vgs=10V, ID= 6A	RDS(ON)		0.65	0.85	Ω
Dynamic Characteristics						
Input Capacitance		Ciss	-	1480	1900	
Output Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	Coss	-	200	270	pF
Reverse Transfer Capacitance	1	Crss	-	25	35	
Switching Characteristics						
Turn-On Delay Time	V _{DD} =325V, I _D =12A, R _G =25Ω, (Note 1,2)	td(on)	_	30	70	ns
Turn-On Rise Time		tr		115	240	
Turn-Off Delay Time		td(off)		95	200	
Turn-Off Fall Time]	t⊧		85	180	
Switching Characteristics						
Total Gate Charge		QG		42	54	nC
Gate-Source Charge	Vps=520V, lp=12A, Vgs=10V (Note 1,2)	Qgs		8.6		
Gate-Drain Charge		Q _{GD}		21		
Drain-Source Diode Characteristics And M	laximum Ratings					
Drain-Source Diode Forward Voltaage	Is=12A, Vgs=0V	VsD			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		ls			12	
Maximum Pulsed Drain-Source Diode Forward Current	V _{GS} =0V, I _S =12A, dI _F /dt=-100A/µs (Note 1)	Іѕм	-		48	A
Reverse Recovery Time		trr		380		ns
Reverse Recovery Charge		Qrr		3.5		μC

- Social any independent of operating temperature

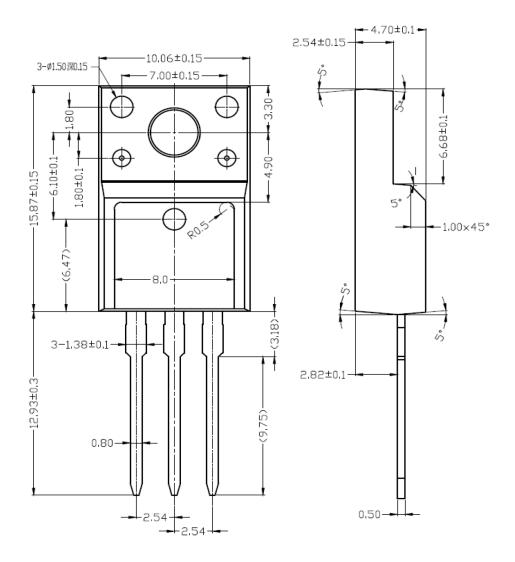
Dimensions: Millimetres



N Channel MOSFET



Outline Dimensions



Part Number Table

Description	Part Number		
N Channel MOSFET, 650V, 12A, TO-220F	HMF12N65S		

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